

What is claimed is:

- 1 1. A structure for providing resilient interconnections in a wafer level
2 package, comprising a conductive pad that overlays an air space, wherein at
3 least a portion of the air space extends laterally beyond the conductive pad.
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- 1 2. The structure as claimed in claim 1, wherein the air space
2 comprises a geometric structure having a plurality of perimeter interconnect
3 support structures for the conductive pad.
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- 1 3. The structure as claimed in claim 2, wherein at least one perimeter
2 interconnect support structure also supports a conductive line electrically
3 connected to the conductive pad.
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- 1 4. The structure as claimed in claim 3, wherein the conductive line is
2 a metal wire.
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- 1 5. The structure as claimed in claim 1, wherein a major axis of the air
2 space is radial to a center of the wafer level package.
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- 1 6. The structure as claimed in claim 1, wherein a major axis of the air
2 space is not radial to a center of the wafer level package.
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1 7. The structure as claimed in claim 2, wherein at least one perimeter
2 interconnect support structure also supports a conductive line electrically
3 connected to the conductive pad.

1 8. The structure as claimed in claim 7, wherein the at least one
2 perimeter interconnect support structure is positioned relative to a center of the
3 conductive pad less than or equal to about 60 degrees of the major axis.

1 9. A method for making a structure for providing resilient
2 interconnections in a wafer level package, comprising the steps of:

- 3 A. forming a cavity having a first area on a semiconductor
4 substrate;
5 B. filling the cavity with a removable material;
6 C. forming a conductive layer over the removable material;
7 D. patterning the conductive layer to form a conductive pad;
8 E. removing the removable material to form an air space below
9 the conductive pad; and
10 F. forming an interconnection material on the conductive pad,
11 whereby at least a portion of the air space extends laterally beyond the
12 conductive pad.

1 10. The method as claimed in claim 9, wherein the removable material
2 is planarized before forming the conductive layer.

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1 11. The method as claimed in claim 10, wherein the planarization is
2 carried out by either an etch-back process or a CMP process.

1 12. The method as claimed in claim 9, wherein the removable material
2 is material selected from the group consisting of a monomeric material, a
3 polymeric material, and an elastomeric material.

1 13. The method as claimed in claim 9, wherein the removable material
2 is a B-stage-able material.

1 14. The method as claimed in claim 9, wherein the cavity is formed by
2 depositing a dielectric layer and thereafter patterning the dielectric layer.

1 15. The method as claimed in claim 14, wherein the patterning of the
2 dielectric layer is carried out using a photolithographic process.

1 16. The method as claimed in claim 9, wherein after forming the
2 conductive layer, a dielectric layer is deposited over the conductive layer.

1 17. The method as claimed in claim 9, wherein after forming the air
2 space, a protective layer is deposited on a top and bottom surface of the
3 conductive pad.

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1 18. The method as claimed in claim 17, wherein the protective layer is
2 carried out by an electroless plating method.

1 19. The method as claimed in claim 18, wherein the protective layer is
2 formed using a metal. B

1 20. The method as claimed in claim 19, wherein the metal is selected
2 from the group consisting of gold and nickel.

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